



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
Dual Silicon Transistor**

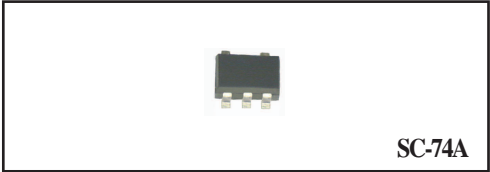
VOLTAGE 20 Volts CURRENT 300 mAmpere

CHT1544RNGP

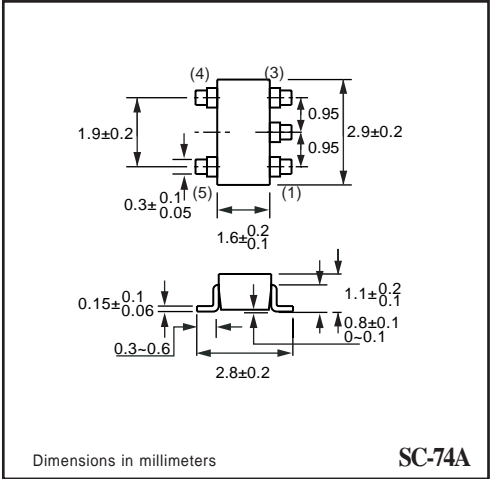
APPLICATION
* Switching circuit, Inverter, Interface circuit, Driver circuit.

FEATURE
* Small surface mounting type. (SC-74A)
* High current gain.
* Suitable for high packing density.
* Low collector-emitter saturation.
* High saturation current capability.
* Both the NPN digital silicon transistor in one package.
* Built in bias resistor(R1=2.2kΩ, Typ.)

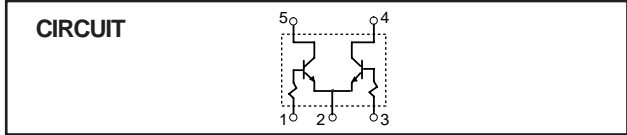
MARKING
*HFE(A) : 44A
*HFE(B) : 44B



SC-74A



SC-74A



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Vcbo	Collector-Base voltage		50	V
Vceo	Collector-Emitter voltage		20	V
Vebo	Emitter-Base voltage		25	V
Ic	Collector current		300	mA
Pd	Collector Power dissipation	T _{amb} ≤ 25 °C, Note 1	300	mW
Tstg	Storage temperature		-55 +150	°C
Tj	Junction temperature		+150	°C
RθJ-s	Thermal resistance , Note 1	junction - soldering point	350	°C/W

Note

- Total rating

RATING CHARACTERISTIC (CHT1544RNGP)

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	Collector cutoff current	V _{CB} =50V	–	–	0.1	uA
I _{EBO}	Emitter cutoff current	V _{EB} =25V	–	–	0.1	uA
V _{CE(sat)}	Collector-emitter saturation voltage	I _C /I _B =10mA/1mA	–	–	0.1	V
h _{FE}	DC current gain	I _C =4mA; V _{CE} =2.0V	200	–	1200	
R ₁	Input resistor		1.54	2.2	2.86	KΩ
f _T	Transition frequency	I _C =4mA, V _{CE} =6.0V	–	30	–	MHz

Note

1.hFE Classification A: 200 to 700, B: 350 to 1200

RATING CHARACTERISTIC CURVES (CHT1544RNGP)

Typical Electrical Characteristics

Fig.1 DC current gain vs. collector current

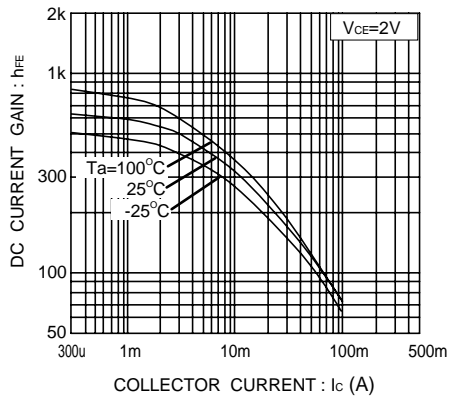


Fig.2 Collector-emitter saturation voltage vs. collector current

